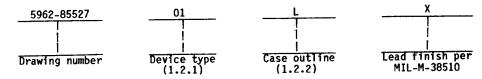
REVISIONS APPROVED DATE DESCRIPTION LTR 29 June Change output delay values in Α 1.2.1. 1987 Minor changes in table I and on figure 2. Update vendor's part numbers. Editorial changes throughout. REV PAGE Α Α Α REV **REV STATUS** 10 13 11 4 5 OF PAGES PAGES 2 **Defense Electronics** ndra Roonly This drawing is available for use by **Supply Center** all Departments and Agencies of the BY Dayton, Ohio Department of Defense MICROCIRCUIT, DIGITAL, BIPOLAR, TITLE: 2K X 8 BIT REGISTERED PROM, MONOLITHIC SILICON Original date of drawing: CODE IDENT. NO. DWG NO. SIZE 5962-85**5**27 6 November 1986 14933 Α OF 21 REV PAGE AMSC N/A 5962-E417

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

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- 1.1 <u>Scope</u>. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".
 - 1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function	Clock-to- output delay
01	27\$45	2048 x 8 bit registered PROM with programmable INITIALIZE (Asynchronous)	30 ns
02	27S45A	2048 x 8 bit registered PROM with programmable INITIALIZE (Asynchronous)	25 ns
03	27S47	2048 x 8 bit registered PROM with programmable INITIALIZE (Synchronous)	30 ns
04	27S47A	2048 x 8 bit registered PROM with programmable INITIALIZE (Synchronous)	25 ns

1.2.2 <u>Case outlines</u>. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter	Case outline
K	F-6 (24-lead, 3/8" x 5/8"), flat package
L	D-9 (24-lead, 1/4" x 1 1/4"), dual-in-line package
X	C-12 (32-terminal, .450" x .550"), rectangular chip carrier package
3	C-4 (28-terminal, .450" x .450"), square chip carrier package

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1.3 Absolute maximum ratings.

```
-0.5 V dc to +7.0 V dc
Supply voltage range - - - - - - - - - - -
DC input voltage _ - - - - - - - - - - - - - - - DC voltage applied to outputs _ - - - - - - -
                                                           -0.5 V dc to +5.5 V dc
                                                           -0.5 V dc to +5.5 V dc
-30 mA to +5.0 mA
-65°C to +150°C
DC input current - - - - - - - - - - - - -
Storage temperature range - - - - - - -
Maximum power dissipation (PD) \underline{1}/; - - - - -
                                                           1.02 W
Lead temperature (soldering, 10 seconds) - - - Thermal resistance, junction-to-case (θ<sub>JC</sub>): 2/
                                                           +300°C
                                                           53°C/W) see MIL-M-38510, appendix C 40°C/W 3/
  Case K - - - - - - - - - - - - - - -
  Case X - - - - - - - - - - - - - - -
                                                           80°C/W
+175°C
  Case 3 - - - - -
Junction temperature (T_{,j}) - - - - - - - -
DC voltage applied to outputs
                                                           21 V dc
  during programming - - -
DC current into outputs during
                                                           250 mA dc
  programming (max duration of 1.0 s) - - - -
```

1.4 Recommended operating conditions.

```
Supply voltage (V_{CC}) - - - - - - - - - - - - 4.5 V dc minimum to 5.5 V dc maximum Minimum high level input voltage (V_{IL}) - - - 2.0 V dc  
Maximum low level input voltage (V_{IL}) - - - - 0.8 V dc  
Case operating temperature range (T_C) - - - - 55°C to +125°C
```

2. APPLICABLE DOCUMENTS

2.1 Government specification and standard. Unless otherwise specified, the following specification and standard, of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510

- Microcircuits, General Specification for

STANDARD

MILITARY

MIL-STD-883

- Test Methods and Procedures for Microelectronics

(Copies of the specification and standard required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

 $\overline{1/}$ Must withstand the added PD due to short circuit test (e.g., IOS). $\overline{2/}$ Heat sinking is recommended to reduce the junction temperature.

2/ Heat sinking is recommended to reduce the junction temperature.
3/ When a thermal resistance value for this case is included in MIL-M-38510, appendix C, that value shall supersede the value indicated herein.

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3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction and physical dimensions shall be as specified in MIL-M-38510 and herein.
 - 3.2.1 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.2 Logic diagram. The logic diagram shall be as specified on figure 2.
 - 3.2.3 Truth table.
- 3.2.3.1 Unprogrammed devices. Testing to the applicable truth table, or alternate testing as specified in 4.3.1c, shall be used for unprogrammed devices for contracts involving no altered item drawing. When testing is required in accordance with 4.3 herein, the devices shall be programmed by the manufacturer prior to test in a checkerboard pattern (a minimum of 50 percent of the total number of bits programmed) or to any altered item drawing pattern which includes at least 25 percent of the total number of bits programmed.
- 3.2.3.2 <u>Programmed devices</u>. The requirements for supplying programmed devices are not part of this drawing.
 - 3.2.4 Case outline. The case outline shall be in accordance with 1.2.2 herein.
- 3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified, the electrical performance characteristics are as specified in table I and apply over the full recommended case operating temperature range.
- 3.4 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in 6.4 herein
- 3.5 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in 6.4. The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall state that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.6 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.7 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.8 <u>Verification and review</u>. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.9 Processing options. Since the PROM is an unprogrammed memory capable of being programmed by either the manufacturer or the user to result in a wide variety of PROM configurations, two processing options are provided for selection, using an altered item drawing.
- 3.9.1 Unprogrammed PROM delivered to the user. All testing shall be verified through group A testing as defined in 3.2.3.1, tables II and III. It is recommended that users perform subgroups 7 and 9 after programming to verify the specific program configuration.
- 3.9.2 Manufacturer-programmed PROM delivered to the user. All testing requirements and quality assurance provisions herein, including the requirements of the altered item drawing shall be satisfied by the manufacturer prior to delivery.

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	TABLE	I. Elec	trical	performance cha	aracteris	tics.			
Test	 Symbol 	-55 4.5	5 γ < γ C	ns $\frac{1}{4}$ $\frac{4}{125}$ °C $\frac{4}{125}$ °C $\frac{4}{$	 Device type 	 Group A subgroup: 		its Max 	Unit
Output high voltage	I v _{OH}	V _{CC} = 4.	.5 V, [H or V _I 2.0 mA	L•	A11	1, 2, 3	2.4	 	V
Output low voltage	VOL	V _{CC} = 4.	.5 V, I _O IH or V _I	L = 16 mA L	A11	1, 2, 3		0.50	 V
Input high voltage	AIH	2/ 3/			A11	1, 2, 3	2.0	 	 V
Input low voltage	VIL	 <u>2</u> / <u>3</u> / 			 A11 	1, 2, 3		 0.8 	V
Input clamp voltage	AIC	V _{CC} = 4	.5 V, I _I	N = -18 mA	A11	1, 2, 3		-1.2	V
Input low current	IIL	V _{CC} = 5 V _{IN} = 0	.5 V, .45 V		A11 	1, 2, 3	 	 250 	 mA
Input high current	IIIH	V _{CC} = 5	.5 V, V _I	N = 5.5 V	A11	1, 2, 3		 40 	l μ Α
Output short-circuit current	I I OS	$ V_{CC} = 5.5 \text{ V}, V_{OUT} = 0 \text{ V}$			A11	1, 2, 3	-20	 -90 	l mA
Power supply current	Icc	VCC = 5 All inpu	.5 V, uts = GN	D	A11	1, 2, 3	 	 185 	l mA
Output leakage current	ICEX	V _{CC} = 5.	.5 V,	V ₀ = 5.5 V	All	1, 2, 3		40	μA
	 	V _E = 2	.4 V	$v_0 = 0.4 \text{ V}$	A11	1, 2, 3		-40	μ Α
Functional tests		 See 4.3	.1d		A11	7,8			
Input capacitance	CIN	V _{IN} = 2.0 V, f = 1.0 MHz			A11	 4 	 	8.0	 pF
Output capacitance	COUT	V ₀ uT = 3	2.0 V, f	= 1.0 MHz	A11	4		15.0	pF
See footnotes at end of	table.								
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Test	Symbol	-55	conditions C < T _C < V < V _{CC} < otherwise	+T25°C	İ	Device type		roup ogro		Limi Min	ts Max	Unit	
ddress to K high,	TAVKH		See figure			02, 04	9,	10,	11 (45		ns	
] 			1	01, 03	9,	10,	11	50		ns	
ddress to K high, hold time	TKHAX	T [!			 	A11	9,	10,	11	0		ns	
elay from K high to output valid, for	TKHQV1	† ! !			T 1	02, 04	9,	10,	11		25	ns	
initially active outputs (high or low)	 	† †			 	01, 03	9,	10,	11		30	ns	
	T TKHKL, TKLKH	T ! !			 	All	9,	10,	11	20		ns	
SS to K high setup time	TGSVKH	T ! !			! ! !	All	9,	10,	11	15		ns	
S to K high hold time	 TKHGSX 	T !			! ! !	A11	 9, 	10,	11	5.0		ns	•
output valid (high	 TILQV 	T ! !			 	01	1 9, 	10,	11	! ! !	40	ns	
or low) <u>7</u> /		! !				02	9,	10,	11	<u> </u>	35	ns	
Asynchronous I recovery to K (high)	 TIHKH				 		<u> </u>		11		 	ns	
<u>1</u> /		† 			j 1 1	02	9,	10,	11	20	! 	ns	
Asynchronous T pulse width (low) 7/	 - TILIH 				 	01, 02	9, 	10,	11	30	 	ns	
	[1					1				İ		
See footnotes at end of	table.												
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I AB	1. <u>F</u>	lectrical performance character	136163 -	Continued.		-
Test	 Symbol 	Conditions $1/$ $-55^{\circ}C \le T_{C} \le +125^{\circ}C$ $4.5 \text{ V} \le \text{ V}_{CC} \le 5.5 \text{ V}$ (unless otherwise specified)	 Device type 	 Group A subgroups 	Limits Min Max 	Unit
IS to K high setup	 TISVKH	 6/ See figure 3	03	9, 10, 11	35	ns
time $8/$		 	04 	9, 10, 11	30 i	ns
TS to K high hold time	TKHISX	T 	 03, 04 	 9, 10, 11 	 0	 ns
Delay from K high to output valid for	TKHQV2	Ť -	01, 03	9, 10, 11	35	ns
initially high-Z outputs		 	02, 04	9, 10, 11	30	ns
Delay from G low to	 TGLQV	† 	01, 03	 9, 10, 11 	35	i ns
output valid (high or low)	1	 	02, 04	9, 10, 11	30	ns
Delay from K high to	T TKHQZ	T 	01, 03	9, 10, 11	35 	ns
output high-Z <u>9</u> /	 	j 	02, 04	9, 10, 11	30	ns
Delay from G high to	I I TGHQZ	T 	01, 03	9, 10, 11	35	ns
output high-Z <u>9</u> /	1		1 02, 04	9, 10, 11	30	ns

1/ All voltages given are referenced to the test system ground for ac and functional testing. Voltages given for dc testing are referenced to the microcircuit ground terminal.

2/ These are absolute voltages with respect to device ground pin and include all overshoots due to system or tester noise. Do not attempt to test these values without suitable equipment.

3/ V_{IL} and V_{IH} threshold levels are guaranteed for 0.8 V and 2.0 V respectively during dc testing. For ac and functional testing V_{IL} and V_{IH} limits of -0.2 V and 4.0 V are implemented to allow for noise margins needed in a high speed, automated test equipment environment, when fast switching of multiple I/O's is encountered.

 $\underline{4}$ / Only one output should be shorted at a time. Duration of the short circuit should not be more

than one second. 5/ These parameters are not 100 percent tested, but are evaluated at initial characterization and at any time the design is modified where capacitance may be affected.

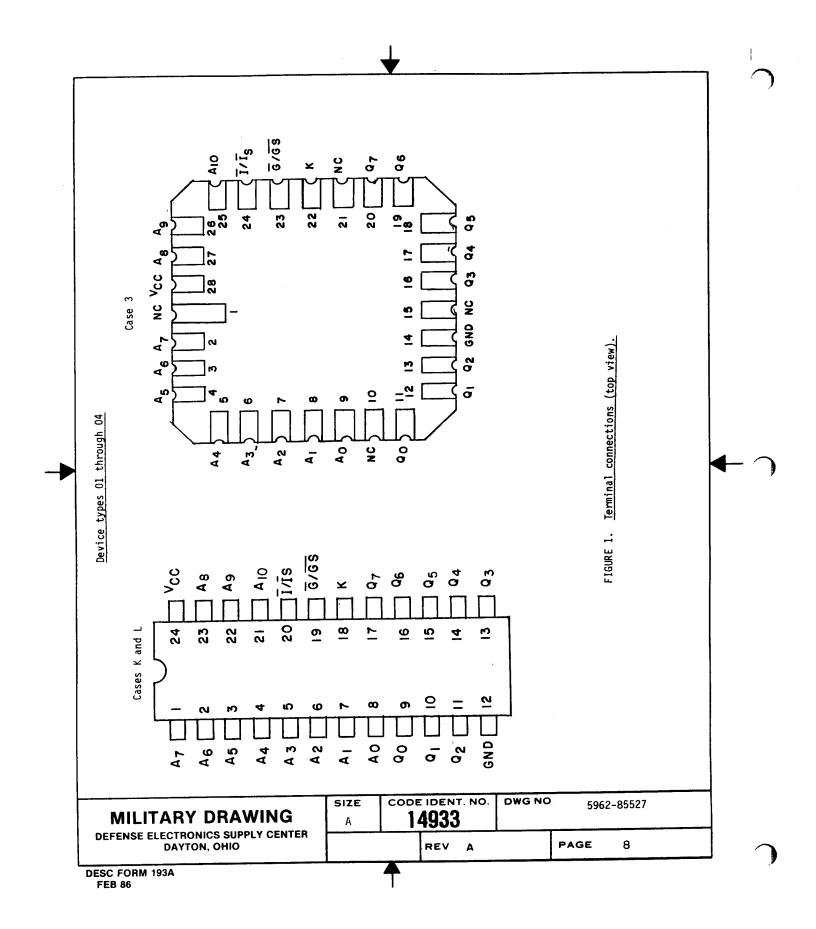
6/ AC tests are performed with input 10 to 90 percent rise and fall times of 5 ns or less.

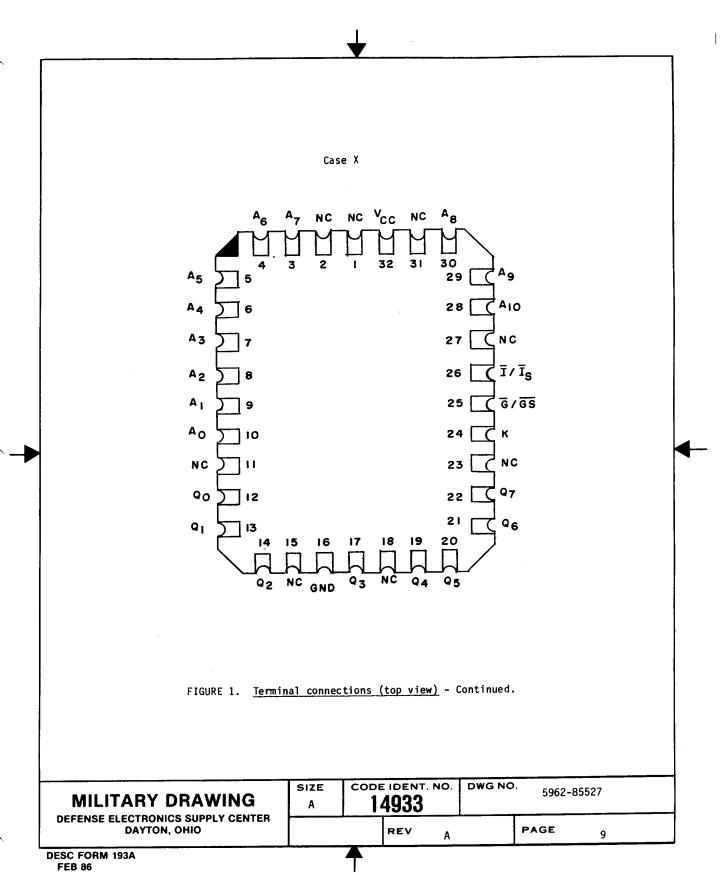
7/ Applies only when programmable initialize is in the asynchronous operation mode.

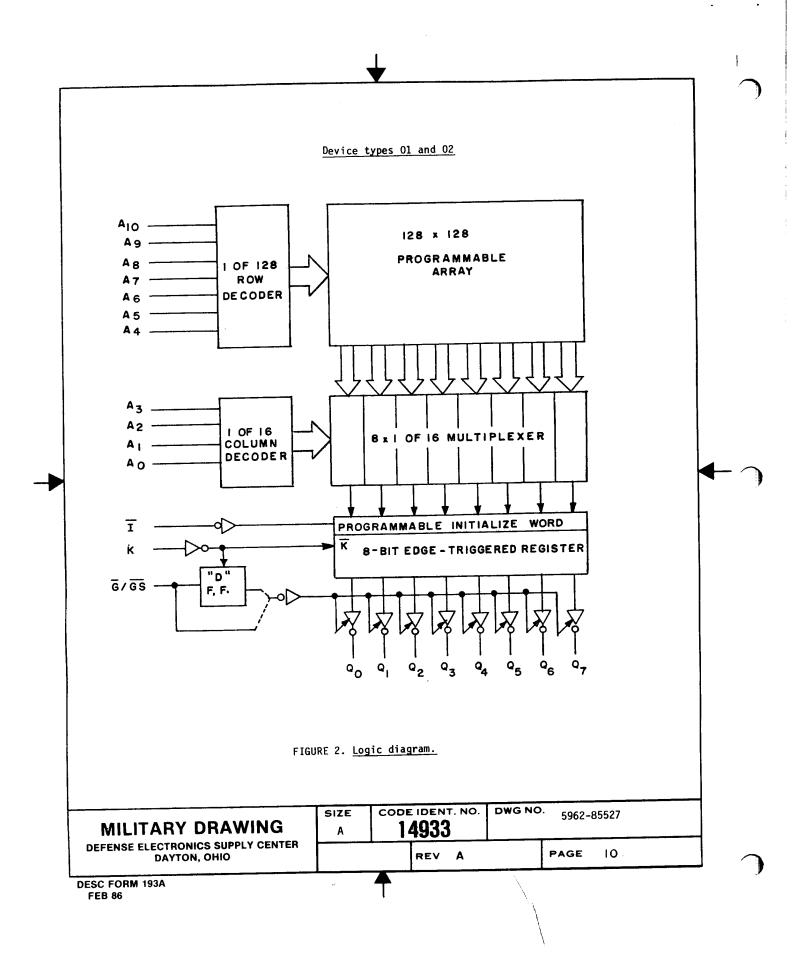
8/ Applies only when programmable initialize is in the synchronous operation mode.

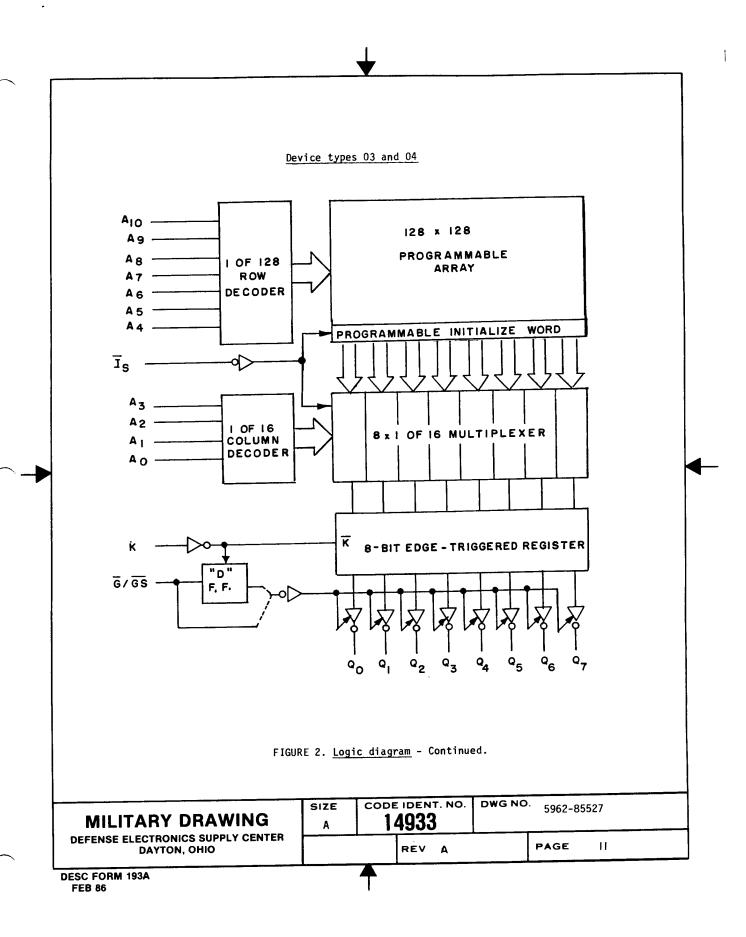
 $\overline{9}/$ TKHQZ and TGHQZ are measured to the V_{OH} -0.5 V and V_{OL} +0.5 V output levels respectively. All other switching parameters are tested from and to the 1.5 V threshold levels.

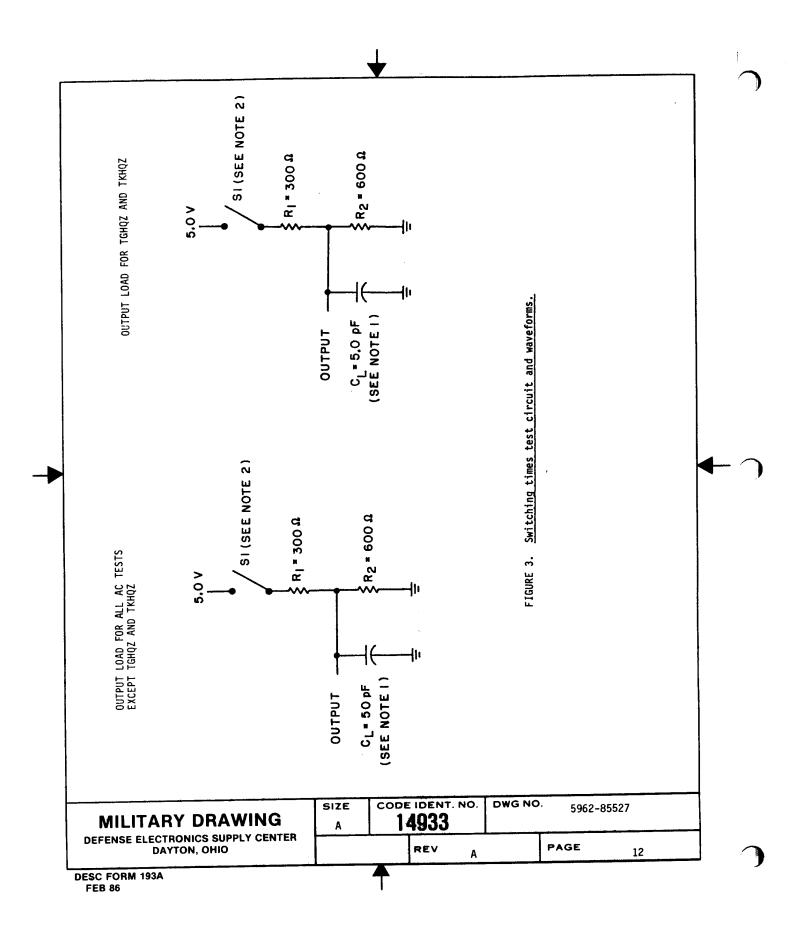
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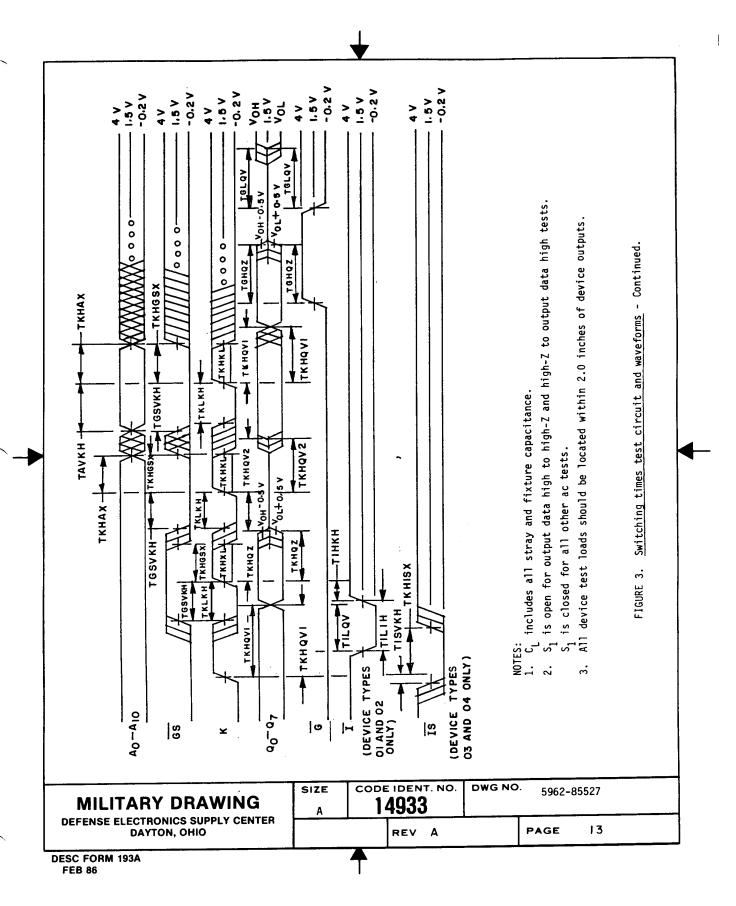












4. QUALITY ASSURANCE PROVISIONS

- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test (method 1015 of MIL-STD-883).
 - (1) Test condition C or D using the circuit submitted with the certificate of compliance (see 3.5 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
 - c. All devices processed by the manufacturer to an altered item drawing shall be programmed prior to burn-in.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method $\overline{5005}$ of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

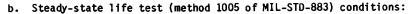
4.3.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Unprogrammed devices shall be tested for programmability and ac performance compliance to the requirements of group A, subgroups 9, 10, and 11. Either of two techniques is acceptable:
 - (1) Additional built-in test circuitry which allows the manufacturer to verify programmability and ac performance without programming the user array. If this is done, the resulting test patterns shall be verified on all devices in group A sample testing, in accordance with MIL-STD-883, method 5005, group A, subgroups 9, 10, and 11.
 - (2) If such compliance cannot be tested on an unprogrammed device, a sample shall be selected to satisfy programmability requirements prior to performing subgroup 9. Twelve devices shall be submitted to programming (see 3.2.3.1). If more than two devices fail to program, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 24 total devices with no more than four total device failures allowed. Ten devices from the programmability sample shall be submitted to the requirements of group A, subgroup 9. If more than two total devices fail, the lot shall be rejected. At the manufacturer's option, the sample may be increased to 20 total devices with no more than four total device failures allowable.
- d. Subgroups 7 and 8 must verify input to output logic combinations.

4.3.2 Groups C and D inspections.

a. End-point electrical parameters shall be as specified in table II herein.

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- (1) Test condition C or D using the circuit submitted with the certificate of compliance (see $3.5\ \text{herein}$).
- (2) $T_A = +125^{\circ}C$, minimum.
- (3) Test duration: 1,000 hours, except as permitted by appendix B of MIL-M-38510 and method 1005 of MIL-STD-883.
- c. The group C, subgroup 1 sample shall include devices tested in accordance with 4.3.1c.

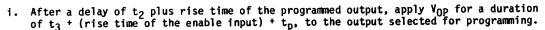
TABLE II. Electrical test requirements.

	
MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	
Final electrical test parameters (method 5004)	1*, 2, 3, 7, 8, 9, 10**, 11**
Group A test requirements (method 5005)	1, 2, 3, 7, 8, 9, 10**, 11**
Groups C and D end-point electrical parameters (method 5005)	1, 2, 3, 7, 8,
Additional electrical subgroups for group C periodic inspections	

- 4.4 Array programming procedure for circuit A. The characteristics on table IIIA and the following procedures shall be used for programming the device.
 - Connect the device in the electrical configuration for programming as shown on figure 4. The waveforms on figure 4 and the programming procedures of table IIIA shall apply to these procedures.
 - b. Terminate all outputs, to VONP through a pull up resistor, R.
 - c. Apply V_{CCP} to V_{CC}.
 - d. Connect $\overline{G}/\overline{GS}$ to V_{ILP} .
 - e. Raise T/I_S input to V_{IHP} .
 - f. Address the PROM with the binary address of the selected word to be programmed.
 - g. Apply VIHP to the G/GS input.
 - h. After a delay of t_1 , apply a low to high transition to the clock (K).

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 ^{*} PDA applies to subgroup 1.
 ** Subgroups 10 and 11, if not tested, shall be guaranteed to the limits specified in table I.



- j. After a delay of t_3 + rise time of the enable input, apply V_{FE} for a duration of t_p + rise time of the programmed output + t_4 , to the G/GS input. G/GS is then reduced to V_{ILP} .
- k. After a delay of t_5 , the opening of the fuse is verified. Each data verification must be preceded by a low-to-high transition of the clock (K). This will load the array data into the output data register. During verification, V_{CC} remains unchanged at V_{CCP} .
- The outputs should be programmed one at a time, since the internal decoding circuitry is capable of sinking only one unit of programming current at a time. Note that the PROM is supplied with fuses generating a low level logic output. Programming a fuse will cause the output to go to a high level logic in the verify mode.
- m. Repeat 4.4a through 4.4k for all other bits to be programmed.
- n. If any unit does not verify data as programmed, it shall be considered a programming reject.

4.4.1 Programming the initialized word.

- a. Repeat steps 4.4a through 4.4d.
- b. Connect T/T_S to V_{ILP} . This deselects the internal programming circuitry for all other addresses.
- c. The initialized word is then programmed, output by output, similar to any other address location, following 4.4g through 4.4n. Address A_0 must be low.

4.4.2 Programming the synchronous enable (\overline{E}_S)

- a. Repeat steps 4.4a through 4.4d.
- b. Connect T/T_S to $V_{\mbox{\scriptsize ILP}}$ This deselects the internal programming circuitry for all other addresses. Address A₀ must be in a logic high state.
- c. A standard programming pulse (in accordance with 4.4g through 4.41) is then applied to output Q. Tie the remaining address inputs to high or low; do not leave any inputs open.
- d. Enable $\overline{G}/\overline{GS}$ fuse verification circuitry by taking the A_0 input to ~ 15 V. This zener level enables on-chip circuitry, which causes the $\overline{G}/\overline{GS}$ fuse to appear as data on all outputs. Therefore, all outputs will be in low logic states when the device is in the asynchronous mode, or high logic states when the device is in the synchronous mode.

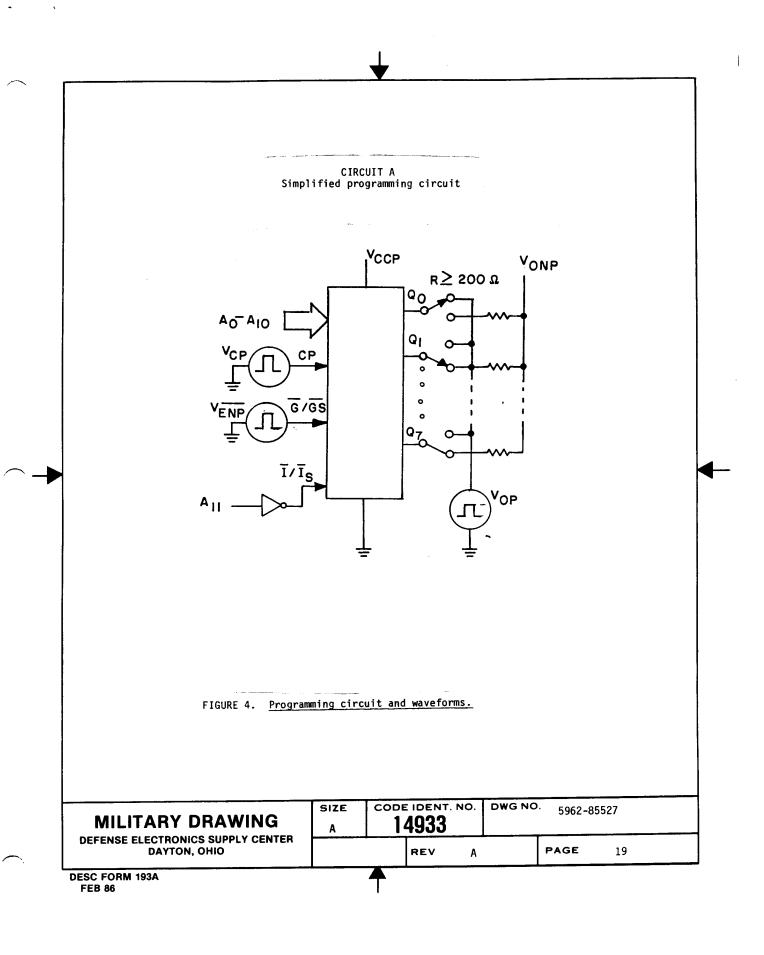
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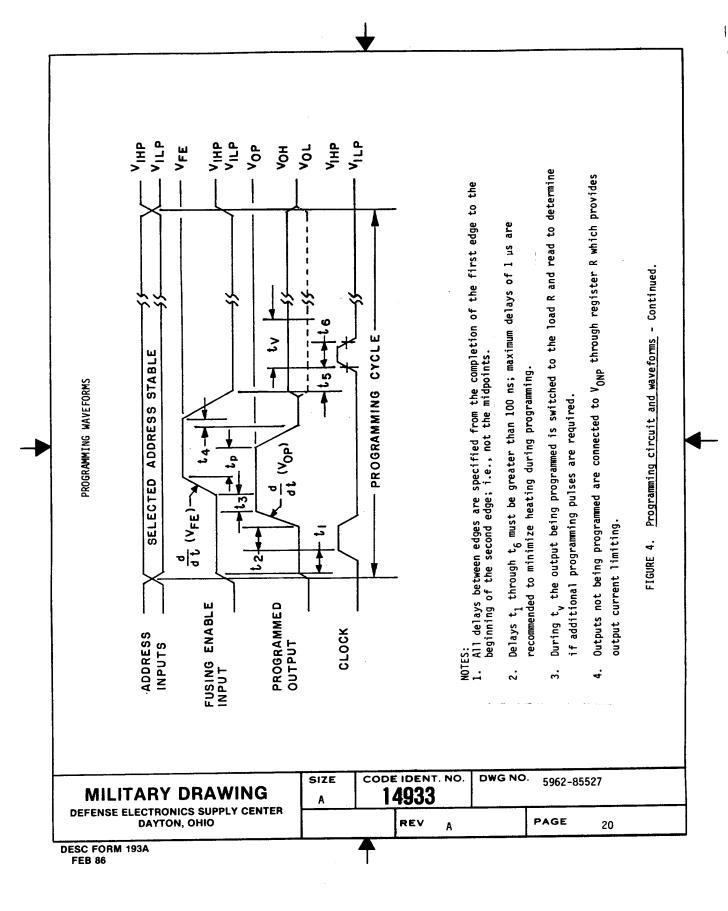
	TABLE IIIA.	Programming characteristic	s for circ	uit A.		
Description Parameter	Parameter	Conditions T _A = +25°C ±5°C 	Limits			Unit
 			Min 	Recom- mended	Max	
Fusing enable voltage	VFE		14.5	15 	15.5	٧
Program voltage	V _{OP}	i At 15 to 200 mA 	19.5 	 20 	20.5	٧
Input high level during programming and verify	V _{IHP}	i] 2.4 	 5 	5.5 5.5 	V
Input low level during l programming and verify	V _{ILP}		0.0	0.3 	0.5	٧
V _{CC} during programming	V _{CCP}	At I _{CC} = 50 to 200 mA	5 	 5.2 	5.5 	٧
Rate of output voltage change i	dV _O p∕dt	1	20	 	250 	V /μs
Rate of fusing enable voltage l	d∀ _{FE} /dt	 	50		1000	V /µ\$
Fusing time first attempt	l t _p	 	40 	i 50 i	100 100	μS
Fusing time subsequent attempts	l t _p		4	5 5	 1000 	ms

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TABLE IIIA. Programming characteristics for circuit A - Continued.						
Description	Parameter	Conditions T _A = +25°C ±5°C	Limits			Unit
;			Min	Recom- mended	Max	
Delays between various level changes	t ₁ -t ₆		100	 	2000	ns
Period during which output is sensed for VBLOWN level	ty			500 500 		ns
Pull-up voltage on outputs not being programmed	YONP I		V _{CCP} -0.3	VCCP	V _{CCP} +0.3	٧
Pull-up resistor on outputs not being programmed	R		0.2	2 	5.1	kΩ
Current into outputs not to be programmed	IONP				20	mA

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- 5. PACKAGING
- 5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.
- NOTES
- 6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5375.
- 6.4 Approved source of supply. An approved source of supply is listed herein. Additional sources will be added as they become available. The vendor listed herein has agreed to this drawing and a certificate of compliance (see 3.5 herein) has been submitted to DESC-ECS.

 Military drawing part number 	 Vendor CAGE number 	Vendor similar part number 1/
5962-8552701LX	34335 34335	AM27S45/BLA AM27S45/BKA
5962-8552701KX 5962-8552701XX	34335 34335	AM27S45/BUA
5962-85527013X	34335	AM27S45/B3A
5962-8552702LX	34335	AM27S45A/BLA
5962-8552702KX	34335	AM27S45A/BKA AM27S45A/BUA
5962-8552702XX 5962-85527023X	34335 34335	AM27545A/BJA
5962-85527025X	i 34335	1 AM27S47/BLA
5962-8552703KX	34335	AM27S47/BKA
5962-8552703XX	34335	AM27S47/BUA
5962-85527033X	34335	AM27S47/B3A
5962-8552704LX	34335	AM27S47A/BLA
5962-8552704KX 5962-8552704XX	1 34335 1 34335	AM27S47A/BKA AM27S47A/BUA
5962-8552704XX 5962-85527043X	34335	AM27S47A/B3A

 $\frac{1}{\text{Tems}}$ acquired to this number may not satisfy the performance requirements of this drawing.

 Vendor CAGE number
 Vendor name and address
 Programming procedure
 Fusible link

 34335
 Advanced Micro Devices, Incorporated 901 Thompson Place Sunnyvale, CA 94088
 A Platinum silicide fuse

MILITARY DRAWING
DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO

SIZE
CODE IDENT. NO. DWG NO.

5962-85527

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